HA166171RFP2/HA166172RFP4 Read/Write Amplifier for Hard Disk Drive

HITACHI

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The HA166171RFP2 and HA166172RFP4 are read/write amplifier designed for use with thin film recording heads. They have the following functions and features.

Functions

- · Read amplifier circuit
- Write driver circuit
- · Constant write current setup circuit
- · 4 channel servo write

Features

- Single power supply +5 V
- Low power

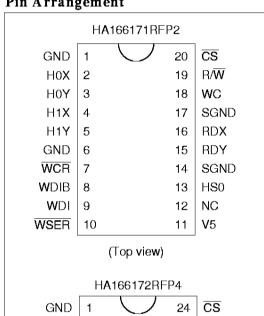
Read: 175 mW (Typ) Idle: 25 mW (Typ)

- Low Noise: $0.54 \text{ nV}/\sqrt{\text{Hz}}$ (Typ)
- · Read amplifier has high differential voltage gain : 380 V/V (Typ)
- · Built-in current and voltage monitors
- ECL compatible interface
- Emitter-follower read amplifier outputs
- Input capacitance: 9 pF (Typ) • Write current range: 5 to 20 mA
- · Self switching damping resistance

Ordering Information

Туре	Channel	Package
H A 166171RFP2	2	FP-20DA
HA166172RFP4	4	FP-24D

Pin Arrangement



R/W HOX 2 23 H0Y 3 22 WC H1X 4 21 **SGND** H1Y 5 20 RDX RDY H2X 6 19 7 **SGND** H2Y 18 НЗХ 8 17 HS₀ H3Y 9 16 HS₁ GND 10 15 **V**5 WCR 11 WSER 14 WDI WDIB 12 13

(Top view)

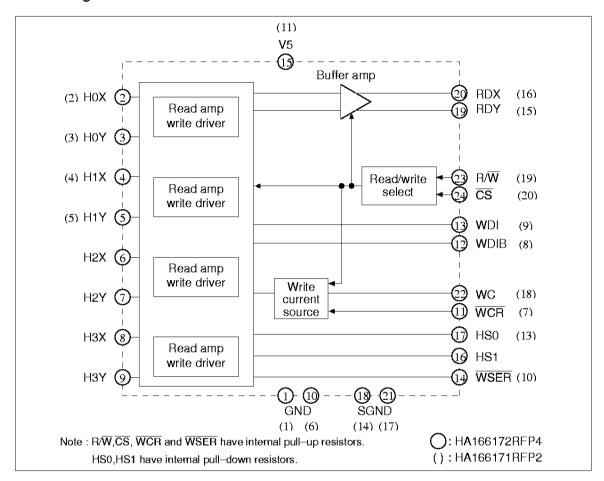


Pin Description

Pin No.

171RFP2	172RFP4	Symbol	Pin Name	Description
1, 6	1, 10	GND	Ground	Ground pins
2, 3	2, 3	H0X, H0Y	Head 0X, 0Y	These pins are connected to the R/\overline{W} head coil of channel 0.
4, 5	4, 5	H1X, H1Y	Head 1X, 1Y	These pins are connected to the R/W head coil of channel 1.
	6, 7	H2X, H2Y	Head 2X, 2Y	These pins are connected to the R/W head coil of channel 2.
	8, 9	НЗХ, НЗҮ	Head 3X, 3Y	These pins are connected to the R/\overline{W} head coil of channel 3.
7	11	WCR	Write current reduce	A low level selects the write current reduce mode. A pin shall be used to reduce write current by 20% from the resistor programmed value.
8, 9	12, 13	W DIB, W DI	Write data input	Write data input pin. The signal is devided in the IC, anddrives the write driver.
10	14	WSER	Servo write switch	When R/W and WSER are set low, all write drivers are selected. Refer to the Mode Select Table.
11	15	V 5	5 V	5 V power supply
13	16 17	HS1 HS0	Head select 1 Head select 0	Input pins for head select signals. The combination of these signals selects one head from head 0 to head 3. Refer to the head select table.
14, 17	18, 21	SGND	Shield ground	Ground for shield of RDX, RDY.
15, 16	19, 20	RDY, RDX	Read amplifier output	Differential output pins for the read amp. The signal read out from the head coil is amplified and provided on these pins.
18	22	WC	Write current setting	Write current setting pin. The write current is defined by the equation below by connecting the external resistance R _{WC} between this pin and GND.
				Write current [mA] = K/R_{WC} [k Ω]
19	23	R/ W	R/W switch	Mode select switch for changing over the bias condition of the head coil.
				A low level selects the write mode, while a high level selects the read mode.
20	24	CS	Chip select	When this line is set high, the circuit goes into the idle state, a low power state. When this line is low, the chip is active.

Block Diagram



Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Rating	Unit	Applicable Terminal
Supply voltage	V 5	-0.3 to +6.0	٧	V5
Write current	l _h	25	m A	
Interface input voltage	V_{IN}	-0.3 to V5 +0.3	V	HS0, HS1, WDI, WDIB WSER, R/W, CS
Read data output current	I _{RO}	-10	m A	RDX, RDY
Operating temperature	Topr	0 to +70	°С	
Storage temperature	Tstg	-55 to +150	°С	
Head voltage swing	V _{HSW}	4.0	Vpp	
Power dissipation	P _T *	900	m W	

Note: * Grass epoxy board (40 mm \times 40 mm), writing density of 20 %, Ta = 70 $^{\circ}$ C

Power Supply ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Supply voltage range	V 5	4.5	_	5.5	V	
+5.5 V supply current	15	_	36	_	m A	Read mode
		_	35 + 1.55 l _h			Write mode
		_	5	_		Idle mode
+5.0 V supply current	15	_	84 + 4.55 l _h	_	mA	Servo write mode

Electrical C haracteristics ($V_{CC} = 5~V, Ta = 25\,^{\circ}C$ unless otherwise specified)

Digital Input

ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Low level input voltage1	V _{IL1}	-0.3	_	0.8	٧	
Low level input current1	I _{IL1}	-100	_	_	μΑ	V _{IL} = 0.4 V
High level input voltage1	V _{IH1}	2.0	_	$V_{CC} + 0.3$	٧	
High level input current1	I _{IH1}	_	_	40	μΑ	V _{IH} = 2.0 V
Low level input voltage2	V_{IL2}	V _{CC} -	1.82	_	V _{CC} –	1.0 V (WDI, WDIB) $1200 \stackrel{?}{\lessgtr} 1200 \stackrel{?}{\lessgtr}$ V_{CC} $WDIB$ $I_{1} = I_{2} = 14 \text{ to } 21 \text{mA}$
High level input voltage2	V_{IH2}	V _{CC} -	0.3	_	V _{CC}	V (WDI, WDIB) Vcc ₹120Ω WDI 120Ω WDII
Differential voltage	V _{DI}	0.65	_	1.82	٧	V _{WDI} – V _{WDIB}
High level input current2	I _{IH2}	_	2	2.6	m A	V _{IH} = V _{CC} (WDI, WDIB)
Read/write transition time	t _{RW}	_	110	150	ns	
Write/read transition time	t _{WR}	_	200	300	ns	
Head select switching delay time	t _{HS}	_	_	1000	ns	Read mode
Chip disable transition time	t _{IR}	_	_	1000	ns	Idle to read
Read/servo write transition time	t _{RS}	_	_	350	ns	R/W to 90 % of write current WSER: L
Servo write/read transition time	t _{SR}	_	_	350	ns	R/W to 90 % of 100 mV read signal envelope, WSER: L

Head Select Table

Mode Select Table

HS1	HS0	Head Selected
L	L	0
	Н	1
Н	L	2
	Н	3

$\mathbf{R}/\overline{\mathbf{W}}$	WSER	Mode
L	L	Servo Write
	Н	Write
Н	L	Read
	Н	

Read Amplifier

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Differential voltage gain	Avd	320	380	440	V/V	f = 300 kHz
Bandwidth	B _W	(90)*1	(150)* ¹	_	MHz	−3 dB
Input noise voltage	Vn	_	(0.54)*1	_	n V /√Hz	f≤ 15 MHz, Inputs shorted
Common mode rejection ratio	CMRR	60	80	_	dB	
Power supply stability	PSRR	45	60	_	-	V_{CC} ±100 mVp-p, f = 5 MHz
Channel separation	Sep	60	80	_	-	Vin = 100 mVp-p on unselected channels and Vin = 0 mVp-p on selected channels, f = 5 MHz
Output offset voltage	Vo	-300	_	300	mV	Inputs shorted
Differential input	Rin	_	0.72	_	kΩ	f = 300 kHz
impedance			0.70		-	f = 5 MHz
Common mode output voltage	Vcom	_	2.8	_	V	
Output source current	loso	_	-10	_	m A	
Output sink current	l _{osi}	_	1.2	_	-	
Input capasitance	C _{IN}	_	(9)*1	(10.8)*1	pF	
Dynamic Range	D_R	1.5	_	_	mVpp	

Note: 1. These values are only for design purpose.

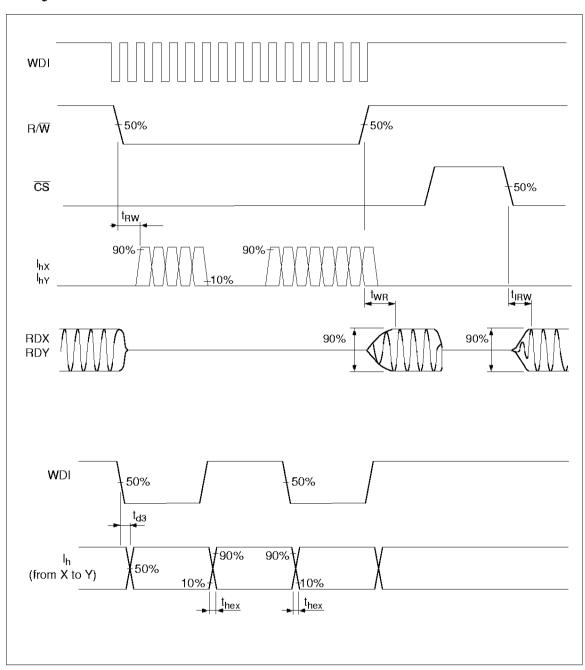
Write Driver

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Write current setting range	l _h	5	_	20	m A	$Rh = 10 \Omega$
Head current rise time	t _{hex}	_	3.5	4.4	ns	Lh = 0μ H, Rh = 0Ω , 10% to 90% point
Head current switching delay time	t _{d3}	_	_	30		Rh = 0Ω , Lh = 0μ H, from 50% point
Head current switching symmetry	t _{d4}	_	_	(1)*1		WDI duty cycle = 50%, rise/fall time = 1 ns
Head current gain	$I_{\rm h}/I_{ m WC}$	_	20	_	A/A	Head current/I _{WC}
WC output voltage	V_{WC}	_	2.7	_	٧	
Write current accuracy1	l _{h1}	9.1	10	10.9	m A	R_{WC} = 5.3 k Ω , Rh = 10 Ω , \overline{WCR} : H
Write current accuracy2	l _{h2}	_	8		mA	$R_{WC} = 5.3 \text{ k}\Omega$, $Rh = 10 \Omega$, \overline{WCR} : L
V _{CC} monitor operative range (Max)	l _{hoff1}	3.6	4.0	4.3	V	R _{WC} = 5.3 kΩ, WCR : H Head current I _h ≤ 0.5 m A
V _{CC} monitor operative range (Min)	l _{hoff2}	_	_	0	_	

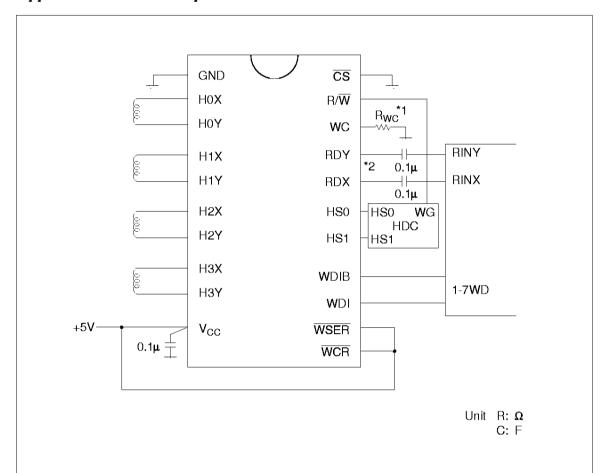
Note: 1. These values are only for design purpose.

^{2.} Write current constant : K = 53 typ.

Timing Waveforms



Application Circuit Example



Notes: 1. External resistance value R_{WC} is determined by following equation.

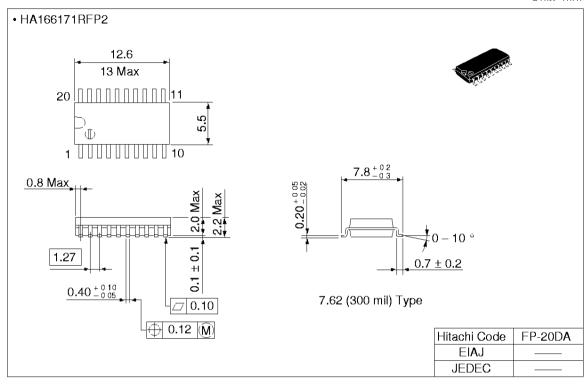
$$R_{WC}\left[k\Omega\right] = \frac{K}{\text{Write current [mA]}}$$

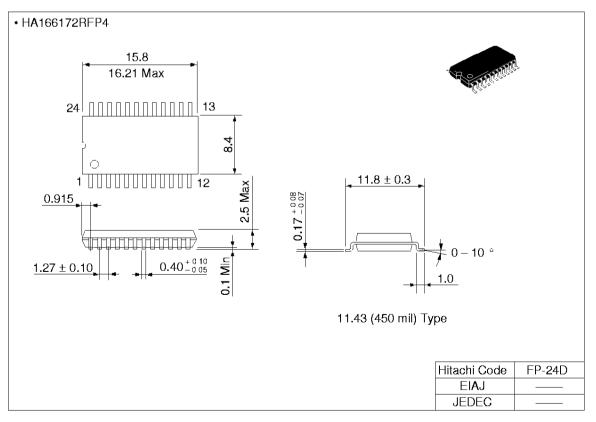
Also, write current ringing on changeover between read and write can be suppressed by locating the resistor R_{WC} as close as possible to the WC pin.

2. When the length of the wiring pattern increases, the RDX and RDY outputs might have some oscillation. This oscillation can be eliminated by inserting series resistors on these outputs as close to the pins as possible.

Package Dimensions

Unit: mm





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